Silicon NPN Epitaxial

HITACHI

ADE-208-226A (Z) 2nd. Edition Mar. 2001

Application

VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 f_T = 11 GHz typ
- High gain, low noise figure
 PG = 15 dB typ, NF = 1.1 dB typ at f = 900 MHz

Outline

SMPAK



- 1. Emitter
- 2. Base
- 3. Collector

Note: Marking is "YZ-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

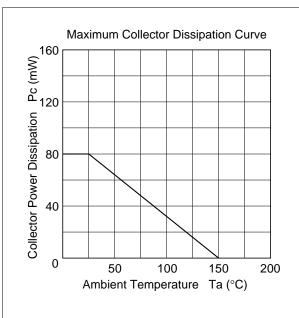


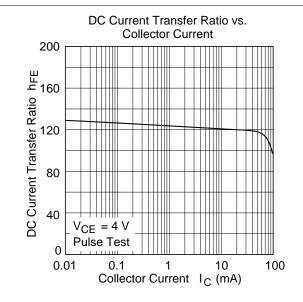
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

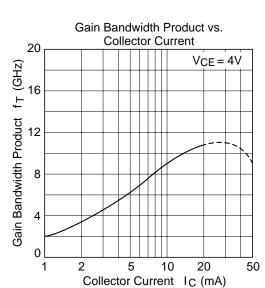
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V _{CEO}	8	V
Emitter to base voltage	V _{EBO}	1.5	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	80	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

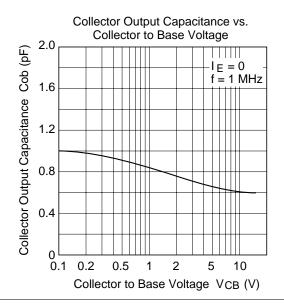
Electrical Characteristics ($Ta = 25^{\circ}C$)

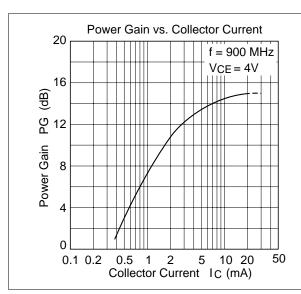
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown boltage	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	_	_	1	μΑ	V _{CB} = 12 V, I _E = 0
	I _{CEO}	_	_	1	mA	V _{CE} = 8 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	V _{EB} = 1.5 V, I _C = 0
DC current transfer ratio	h_{FE}	50	120	250		$V_{CE} = 4 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	0.65	1.15	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0,$ f = 1 MHz
Gain bandwidth product	f⊤	8	11	_	GHz	$V_{CE} = 4 \text{ V}, I_{C} = 20 \text{ mA}$
Power gain	PG	11.5	15	_	dB	$V_{CE} = 4 \text{ V}, I_{C} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.1	2.0	dB	$V_{CE} = 4 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

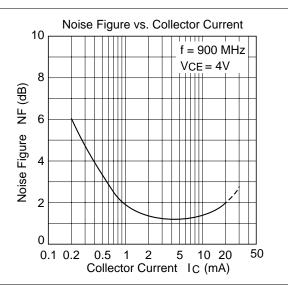




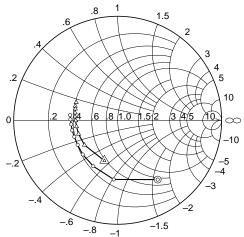






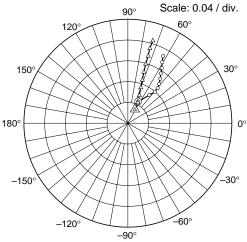


S11 Parameter vs. Frequency



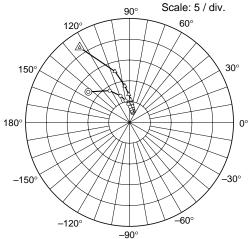
Condition: $V_{CE}=4~V$, $Z_{O}=50~\Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (I C = 5 mA) \triangle (I C = 20 mA)

S12 Parameter vs. Frequency



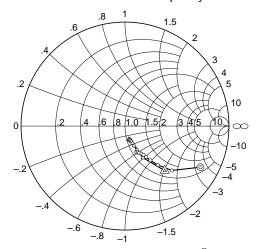
Condition: $V_{CE}=4$ V , $Z_{O}=50$ Ω 200 to 2000 MHz (200 MHz step) Ω (I Ω = 5 mA) Ω (I Ω = 20 mA)

S21 Parameter vs. Frequency

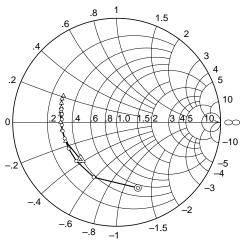


Condition: $V_{CE}=4 \text{ V}$, $Z_{O}=50 \Omega$ 200 to 2000 MHz (200 MHz step) \bigcirc (I C = 5 mA) \triangle (I C = 20 mA)

S22 Parameter vs. Frequency



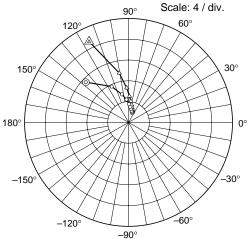
S11 Parameter vs. Frequency



Condition: V_{CE} = 1 V , Z_{O} = 50 Ω 200 to 2000 MHz (200 MHz step) \bigcirc (IC = 5 mA)

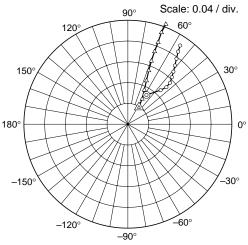
 $\underline{\hspace{1cm}}$ (I C = 20 mA)

S21 Parameter vs. Frequency



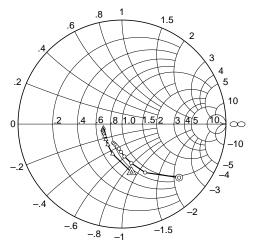
Condition: $\,\text{V}_{\,\text{CE}} \!=\! 1\,\,\text{V}$, Zo = 50 Ω 200 to 2000 MHz (200 MHz step) \bigcirc (IC = 5 mA) Δ (I C = 20 mA)

S12 Parameter vs. Frequency



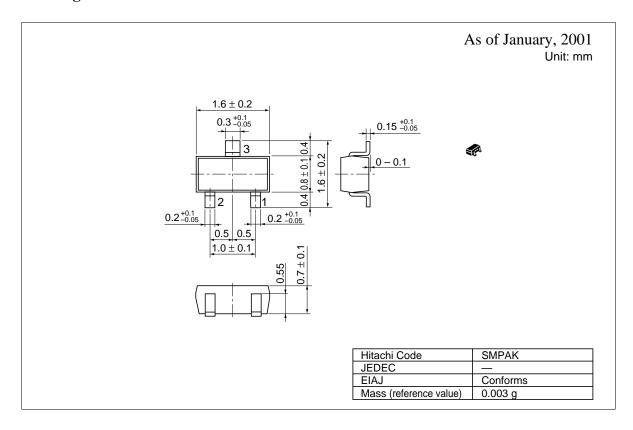
Condition: $V_{CE} = 1 \text{ V}$, $Z_{O} = 50 \Omega$ 200 to 2000 MHz (200 MHz step) ⊚——o (I_C = 5 mA) Δ (I c = 20 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 1 V , Z_{O} = 50 Ω 200 to 2000 MHz (200 MHz step) ⊙ (I_C = 5 mA) (IC = 20 mA)<u>A</u>-

Package Dimensions



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